

**isc N-Channel MOSFET Transistor**
**YTF440**
**FEATURES**

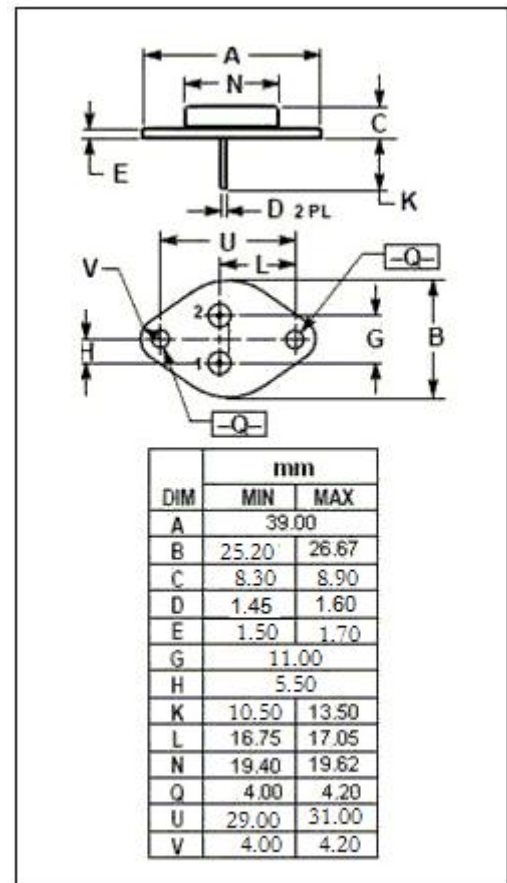
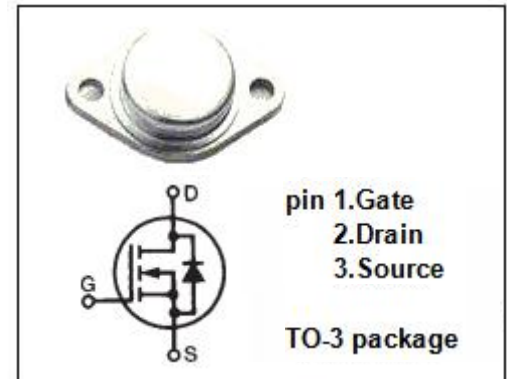
- Drain Current :  $I_D = 8A @ T_C = 25^\circ C$
- Drain Source Voltage :  $V_{DSS} = 500V(\text{Min})$
- Static Drain-Source On-Resistance :  $R_{DS(on)} = 0.85 \Omega (\text{Max})$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**DESCRIPTION**

- motor drive, DC-DC converter, power switch and solenoid drive.

**ABSOLUTE MAXIMUM RATINGS( $T_a = 25^\circ C$ )**

| SYMBOL    | PARAMETER                              | VALUE    | UNIT       |
|-----------|--|----------|------------|
| $V_{DSS}$ | Drain-Source Voltage                   | 500      | V          |
| $V_{GS}$  | Gate-Source Voltage-Continuous         | $\pm 20$ | V          |
| $I_D$     | Drain Current-Continuous               | 8        | A          |
| $I_{DM}$  | Drain Current-Single Pluse             | 32       | A          |
| $P_D$     | Total Dissipation @ $T_C = 25^\circ C$ | 125      | W          |
| $T_J$     | Max. Operating Junction Temperature    | -55~150  | $^\circ C$ |
| $T_{stg}$ | Storage Temperature                    | -55~150  | $^\circ C$ |


**THERMAL CHARACTERISTICS**

| SYMBOL        | PARAMETER                            | MAX | UNIT         |
|---------------|--------------------------------------|-----|--------------|
| $R_{th\ j-c}$ | Thermal Resistance, Junction to Case | 1   | $^\circ C/W$ |

## isc N-Channel MOSFET Transistor

YTF440

## ELECTRICAL CHARACTERISTICS

T<sub>C</sub>=25°C unless otherwise specified

| SYMBOL               | PARAMETER                       | CONDITIONS                                     | MIN | MAX  | UNIT |
|----------------------|---------------------------------|--|-----|------|------|
| V <sub>(BR)DSS</sub> | Drain-Source Breakdown Voltage  | V <sub>GS</sub> = 0; I <sub>D</sub> = 0.25mA   | 500 | --   | V    |
| V <sub>GS(th)</sub>  | Gate Threshold Voltage          | V <sub>DS</sub> = 10V; I <sub>D</sub> = 0.25mA | 2   | 4    | V    |
| R <sub>DS(on)</sub>  | Drain-Source On-Resistance      | V <sub>GS</sub> = 10V; I <sub>D</sub> = 4A     | --  | 0.85 | Ω    |
| I <sub>GSS</sub>     | Gate-Body Leakage Current       | V <sub>GS</sub> = ±20V; V <sub>DS</sub> = 0    | --  | ±0.1 | uA   |
| I <sub>DSS</sub>     | Zero Gate Voltage Drain Current | V <sub>DS</sub> =500V; V <sub>GS</sub> = 0     | --  | 0.25 | mA   |
| V <sub>SD</sub>      | Forward On-Voltage              | I <sub>S</sub> = 8A; V <sub>GS</sub> = 0       | --  | 2    | V    |

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